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(71) Applicant: AGENCY OF IND SCIENCE &

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## (54) PRODUCTION OF THIN FINE CRYSTAL SILICON

(57) Abstract:

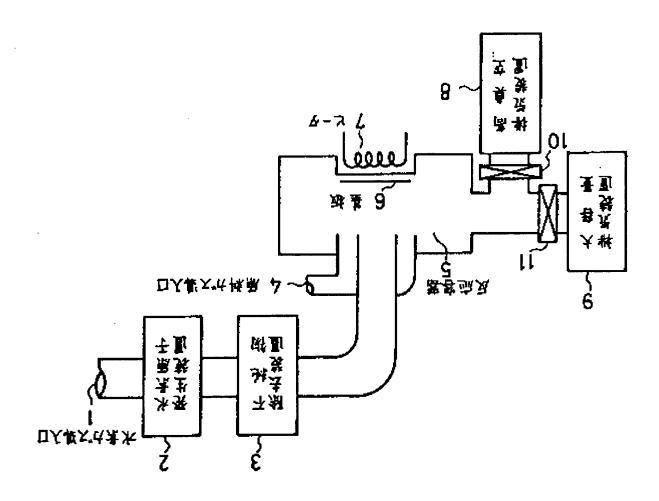
bringing hydrogen atoms having high purity and a gaseous Si material such in a reaction vessel contg. The heated gas gaseous monosilane into reaction crystal Si film having a large crystal grain size and good quality without lattice distortion on a substrate by PURPOSE: To form a thin fine

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and thereafter the hydrogen atoms are On the other hand, the gaseous Si raw quality on the surface of the substrate material such as gaseous monosilane, 5 heated to 50W350°C by a heater 7. hydrogen atoms thereby forming the gaseous disilane or gaseous trisilane material introducing port 4 into the removed by an impurity remover 3 supplied into the reaction vessel 5. thin fine crystal Si film having the gaseous H2 introducing port 1 and concn. by a hydrogen atoms in the stage of the generation thereof are CONSTITUTION: Gaseous H2 is supplied into the vessel through a is supplied through a gaseous raw reactively are generated to a high large crystal grain size and good the electrically neutral hydrogen vessel 5 so as to react with the atoms having high chemical

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